

L Number	Hits	Search Text	DB	Time stamp
1	0	wo-01933312-\$.did.	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:04
2	0	wo-933312-\$.did.	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:05
3	133	daggett.in.	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:17
4	65406	700/\$.ccls. or 345/\$.ccls.	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:18
5	2916	(700/\$.ccls. or 345/\$.ccls.) and (wafer or semiconductor same substrate)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:18
6	959	((700/\$.ccls. or 345/\$.ccls.) and (wafer or semiconductor same substrate)) and (coat\$3 or develop\$4) same (wafer or substrate)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 17:02
7	52	((700/\$.ccls. or 345/\$.ccls.) and (wafer or semiconductor same substrate)) and (coat\$3 or develop\$4) same (wafer or substrate)) and (serial\$3 or sequential\$2) near3 (control\$4 or regulat\$3 or program\$4)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:21
8	2394	(700/\$.ccls. or 345/\$.ccls.) and (coat\$3 or develop\$4) same (wafer or substrate)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:53
9	137147	(serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 17:01
10	356	((700/\$.ccls. or 345/\$.ccls.) and (coat\$3 or develop\$4) same (wafer or substrate)) and ((serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3))	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:37
11	21	((700/\$.ccls. or 345/\$.ccls.) and (coat\$3 or develop\$4) same (wafer or substrate)) and ((serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3)) and interrupt\$3 same (command or subroutine or subprogram or step)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 17:02
12	11	4982694.uref.	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:43
13	2542	(118/\$.ccls. or 396/564-641.ccls. or 134/902.ccls. or 430/\$.ccls.) and (serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3 or program\$4)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:52
14	1058	((118/\$.ccls. or 396/564-641.ccls. or 134/902.ccls. or 430/\$.ccls.) and (serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3 or program\$4)) and (coat\$3 or develop\$4) same (wafer or substrate)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:53

15	14	((118/\$.ccls. or 396/564-641.ccls. or 134/902.ccls. or 430/\$.ccls.) and (serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3 or program\$4)) and (coat\$3 or develop\$4) same (wafer or substrate)) and interrupt\$3 same (command or subroutine or subprogram or step)	USPAT; US-PGPUB; EPO; DERWENT	2003/07/10 16:54
16	33627	(serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3)	EPO; JPO; DERWENT	2003/07/10 17:02
17	141	((serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3)) and (coat\$3 or develop\$4) same (wafer or substrate)	EPO; JPO; DERWENT	2003/07/10 17:02
18	1	((serial\$2 or sequential\$2) near3 (control\$4 or regulat\$3 or operat\$3 or management or process\$3 or execut\$3)) and (coat\$3 or develop\$4) same (wafer or substrate)) and interrupt\$3 same (command or subroutine or subprogram or step)	EPO; JPO; DERWENT	2003/07/10 17:02